Serial Number: 09/471,460 Filing Date: December 22, 1999

Title: USE OF A PLASMA SOURCE TO FORM A LAYER DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

IN THE SPECIFICATION

Page 2 Dkt: 303.932US4

Please amend the specification as follows:

The paragraph beginning at page 1, after the title, labeled "<u>RELATED APPLICATIONS</u>" added in the Preliminary Amendment as follows:

This application contains subject matter related to U.S. application Ser. No. 09/470,650, now U.S. Pat. No. 6,716,769, which is also a divisional of pending U.S. application Ser. No. 09/046,835, now U.S. Pat. No. 6,117,764, mentioned above.

This application also contains subject matter related to U.S. application Ser. No. 09/470,651, now abandoned, which is a continuation of pending U.S. application Ser. No. 09/046,835, now U.S. Pat. No. 6,117,764, mentioned above.